

Power management (dual digital transistors)

EMC4 / UMC4N / FMC4A

●Features

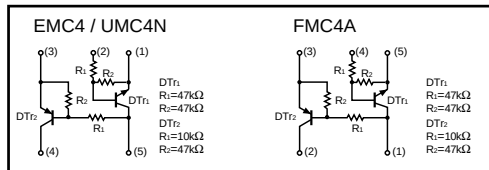
- 1) Both the DTA114Y chip and DTC114E chip in a EMT or UMT or SMT package.
- 2) Ideal for power switch circuits.
- 3) Mounting cost and area can be cut in half.

●Structure

Epitaxial planar type

NPN / PNP silicon transistor (Built-in resistor type.)

●Equivalent circuit

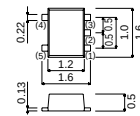


●Packaging specifications

Type	Package	Taping		
	Code	T2R	TR	T148
	Basic ordering unit (pieces)	8000	3000	3000
EMC4	○	—	—	—
UMC4N	—	○	—	—
FMC4A	—	—	—	○

●External dimensions (Units : mm)

EMC4

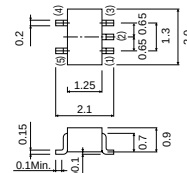


Each lead has same dimensions

ROHM : EMT5

Abbreviated symbol : C4

UMC4N



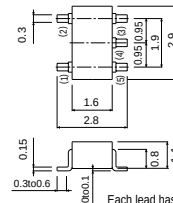
Each lead has same dimensions

ROHM : UMT5

EIAJ : SC-88A

Abbreviated symbol : C4

FMC4A



Each lead has same dimensions

ROHM : SMT5

EIAJ : SC-74A

Abbreviated symbol : C4

Transistors

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits		Unit
			DTr ₁	DTr ₂	
Supply voltage		V _{CC}	50	−50	V
Input voltage		V _{IN}	40	−40	V
			−10	6	
Output current		I _o	30	−100	mA
		I _{c (Max.)}	100	−100	
Power dissipation	EMC4, UMC4N	Pd	150 (TOTAL)		mW *1 *2
	FM4A		300 (TOTAL)		
Junction temperature		T _j	150		°C
Storage temperature		T _{stg}	−55~+150		°C

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

●Electrical characteristics (Ta = 25°C)

DTr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I (off)}	−	−	0.5	V	V _{CC} =5V, I _O =100μA
	V _{I (on)}	3	−	−		V _O =0.3V, I _O =2mA
Output voltage	V _{O (on)}	−	0.1	0.3	V	I _O =10mA, I _I =0.5mA
Input current	I _I	−	−	0.18	mA	V _I =5V
Output current	I _{O (off)}	−	−	0.5	μA	V _{CC} =50V, V _I =0V
DC current gain	G _I	68	−	−	−	V _O =5V, I _O =5mA
Transition frequency	f _T	−	250	−	MHz	V _{CE} =10mA, I _E =−5mA, f=100MHz *
Input resistance	R ₁	32.9	47	61.1	kΩ	−
Resistance ratio	R ₂ /R ₁	0.8	1	1.2	−	−

* Transition frequency of the device

DTr2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I (off)}	−	−	−0.3	V	V _{CC} =−5V, I _O =−100μA
	V _{I (on)}	−1.4	−	−		V _O =−0.3V, I _O =−1mA
Output voltage	V _{O (on)}	−	−0.1	−0.3	V	I _O =−5mA, I _I =−0.25mA
Input current	I _I	−	−	−0.88	mA	V _I =−5V
Output current	I _{O (off)}	−	−	−0.5	μA	V _{CC} =−50V, V _I =0V
DC current gain	G _I	68	−	−	−	V _O =−5V, I _O =−5mA
Transition frequency	f _T	−	250	−	MHz	V _{CE} =10mA, I _E =−5mA, f=100MHz *
Input resistance	R ₁	7	10	13	kΩ	−
Resistance ratio	R ₂ /R ₁	3.7	4.7	5.7	−	−

* Transition frequency of the device

Transistors

●Electrical characteristic curves

DTr1 (NPN)

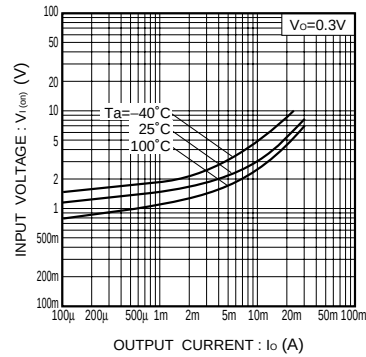


Fig.1 Input voltage vs. output current
(ON characteristics)

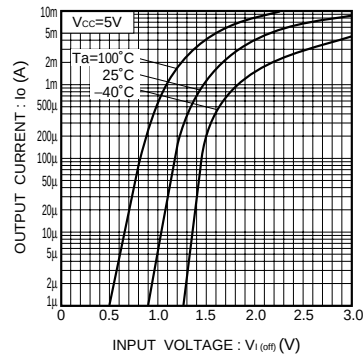


Fig.2 Output current vs. input voltage
(OFF characteristics)

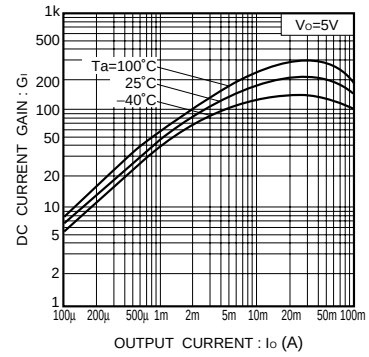


Fig.3 DC current gain vs. output
current

DTr2 (PNP)

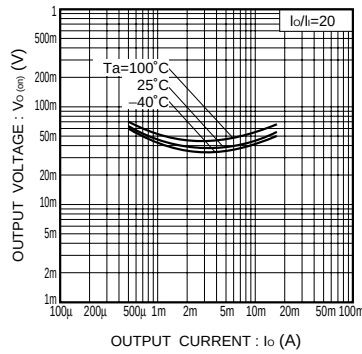


Fig.4 Output voltage vs. output
current

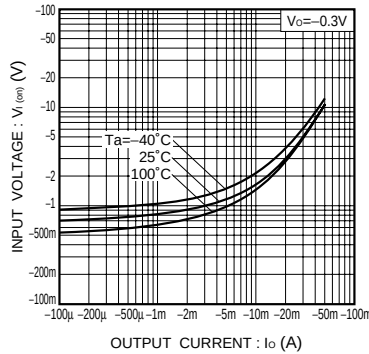


Fig.5 Input voltage vs. output current
(ON characteristics)

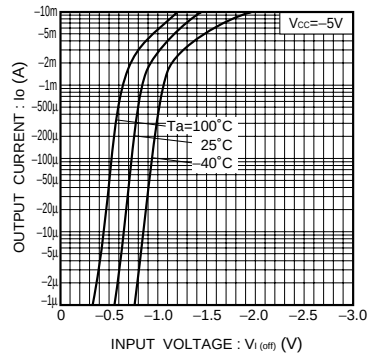


Fig.6 Output current vs. input voltage
(OFF characteristics)

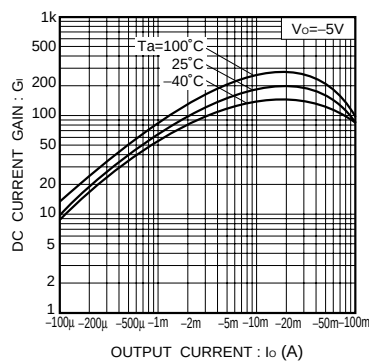


Fig.7 DC current gain vs. output
current

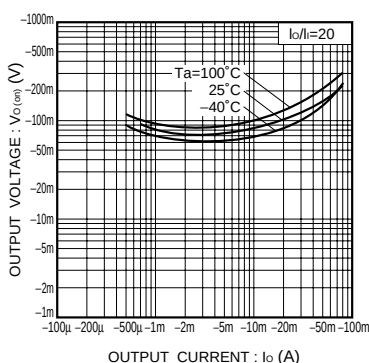


Fig.8 Output voltage vs. output
current